What is claimed is:

SUB A3

1. A multi-finger type ESD protection device comprising:

a semiconductor substrate;

a plurality of first active regions formed separately on the semiconductor substrate; and

a pair of gates formed in each of the first active regions.

2. The device of claim 1, further comprising:

at least one second active region of a predetermined conductive type formed additionally between the first active regions.

A

3. The device of claim 2, wherein the second active region includes an n+ junction connected to Vcc.

4. The device of claim 2, wherein the second active region includes a p+ junction connected to Vss.

5. The device of claim 2, further comprising:

a plurality of drain regions formed in each of the first active regions.

6. The device of claim 5, wherein the drain regions include a pair of drain regions formed at n+ junctions of both end portions of each of the first active regions.

7. The device of claim 1, further comprising:

a plurality of source regions each formed between the pair of gates in each of the first active regions.

8. The device of claim 2, wherein the first and second active regions and the gates extend substantially parallel to each other.

9. The device of claim 8, wherein the first and second active regions and the gates have a substantially same shape.

10. The device of claim 2, further comprising:

a third active region surrounding the first and second active regions.

11. A multi-finger type ESD protection device comprising:

a semiconductor substrate;

a plurality of first active regions formed separately on the semiconductor substrate;

a plurality of gates formed in each of the first active regions; and

at least one predetermined conductive type second active region each formed between two of the first active regions.

12. The device of claim 11, wherein the predetermined conductive type second active region is an n+ junction connected to Vcc.

13. The device of claim 11, wherein the predetermined conductive type second active region is a p+ junction connected to Vss.

14. The device of claim 11, further comprising:

drain regions formed at n+ junctions of both end portions of the first active regions.

15. The device of claim 11, further comprising:

source regions each formed between two gates in each of the first active regions.

16. The device of claim 11, wherein the first and second active regions and the gates extend substantially parallel to each other and have a substantially same shape.

17. The device of claim 11, further comprising:

SUB A7

a third active region surrounding the first and second active regions.

18. A multi-finger type ESD protection device comprising:

a semiconductor substrate;

a plurality of first active regions formed separately on the semiconductor substrate;

a pair of gates formed in each of the first active regions;

drain regions formed at n+ junctions of both end portions of the first active regions;

source regions each formed between the pair of gates in each of the first active regions; and

at least one second active region of a predetermined conductive type, formed between the first active regions.

19. The device of claim 18, wherein the predetermined conductive type second active region includes an n+ junction connected to Vcc.

20. The device of claim 18, wherein the predetermined conductive type second active region includes a p+ junction connected to Vss.

Add A8>

Add B6>